

## Product Overview

### NTLJD3119C: Complementary Power MOSFET 20V

For complete documentation, see the data sheet.

Power MOSFET  
20 V/-20 V, 4.6 A/-4.1 A, Complementary,  
2x2 mm, WDFN Package

#### Features

- Complementary N-Channel and P-Channel MOSFET
- WDFN Package with Exposed Drain Pad for Excellent Thermal Conduction
- Leading Edge Trench Technology for Low On Resistance
- 1.8 V Gate Threshold Voltage
- Low Profile (< 0.8 mm) for Easy Fit in Thin Environments

#### Applications

- Synchronous DC-DC Conversion Circuits
- Load/Power Management of Portable Devices
- Color Display and Camera Flash Regulators

#### Benefits

- Easy Circuit Layout, Circuit Design Flexibility
- Excellent Thermal Conduction

#### End Products

- PDA
- Cellular Phones
- Hard Drives

### Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS(BR)}$ Min (V)	$V_{GS}$ Max (V)	$V_{GS(th)}$ Max (V)	$I_D$ Max (A)	$P_D$ Max (W)	$R_{DS(on)}$ Max @ $V_{GS} = 2.5$ V (m $\Omega$ )	$R_{DS(on)}$ Max @ $V_{GS} = 4.5$ V (m $\Omega$ )	$R_{DS(on)}$ Max @ $V_{GS} = 10$ V (m $\Omega$ )	$Q_g$ Typ @ $V_{GS} = 4.5$ V (nC)	$Q_g$ Typ @ $V_{GS} = 10$ V (nC)	$C_{iss}$ Typ (pF)	Package Type
NTLJD3119CTBG	0.218	Pb-free Halide free non AEC-Q and PPAP	Active	Complementary	Dual	$\pm 20$	8	1	3.8	1.5	N:85, P:135	N:65, P:100	-	5.5	3.7	N: 271, P: 531	WDFN-6

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